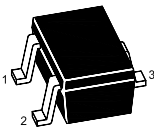


BAS70W / -04W / -05W / -06W

SURFACE MOUNT SCHOTTKY BARRIER DIODE

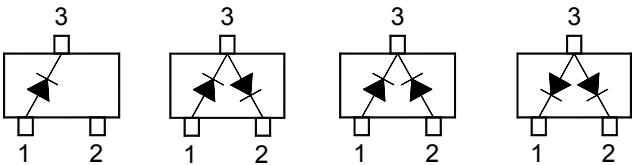
Features

- Low Turn-on Voltage
- Fast Switching



SOT-323 Plastic Package

BAS70W BAS70-04W BAS70-05W BAS70-06W



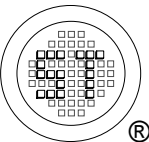
BAS70W Marking Code: **73**
BAS70-04W Marking Code: **74**
BAS70-05W Marking Code: **75**
BAS70-06W Marking Code: **76**

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
DC Blocking Voltage	V_R	70	V
Forward Continuous Current	I_F	70	mA
Peak Forward Surge Current (at $t_p \leq 8.3\text{ ms}$)	I_{FSM}	100	mA
Power Dissipation	P_d	200	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	V_F	-	0.41	V
	V_F	-	1	V
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	70	-	V
Reverse Leakage Current at $V_R = 50\text{ V}$	I_R	-	100	nA
Junction Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_J	-	2	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{rr} = 0.1\text{ }I_R$	t_{rr}	-	5	ns



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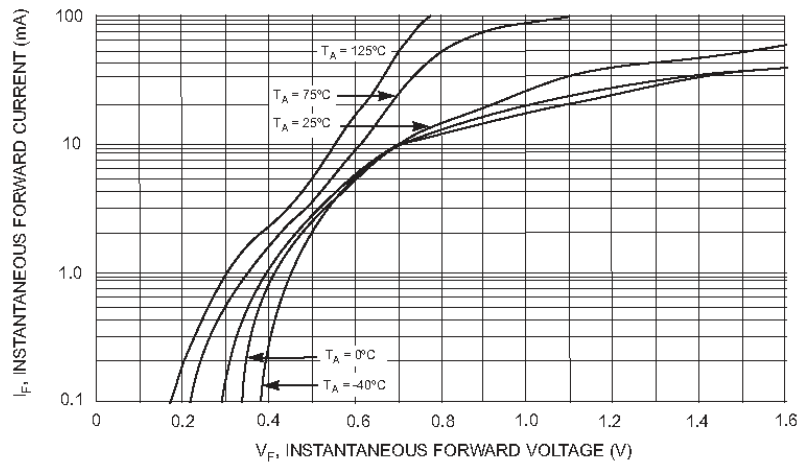


Fig. 1 Typical Forward Characteristics

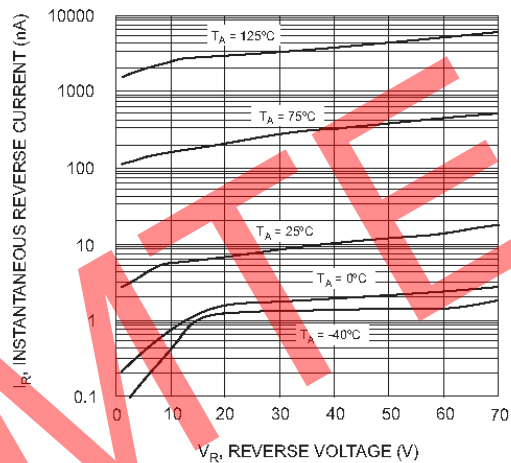


Fig. 2 Typical Reverse Characteristics

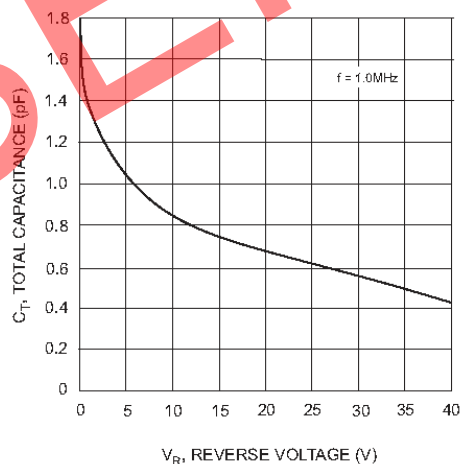


Fig. 3 Typical Capacitance

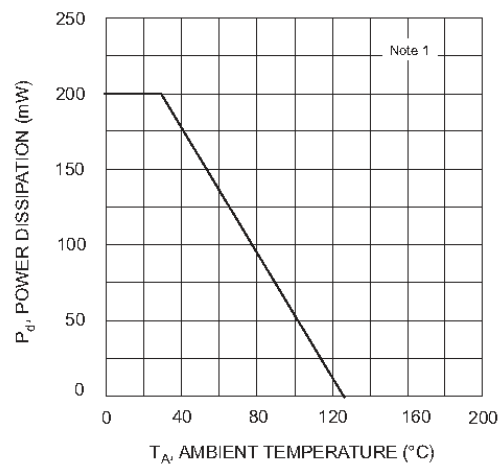
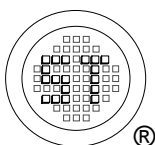


Fig. 4 Power Derating Curve, Total Package



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